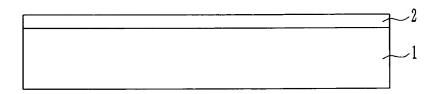
## FIG. 1A (PRIOR ART)



## FIG. 1B (PRIOR ART)

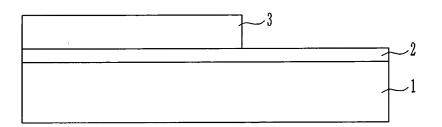


FIG. 1C (PRIOR ART)

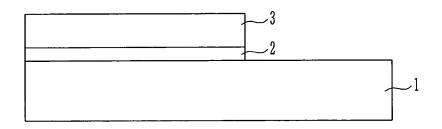


FIG. 1D (PRIOR ART)

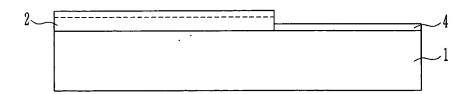


FIG. 2 (PRIOR ART)

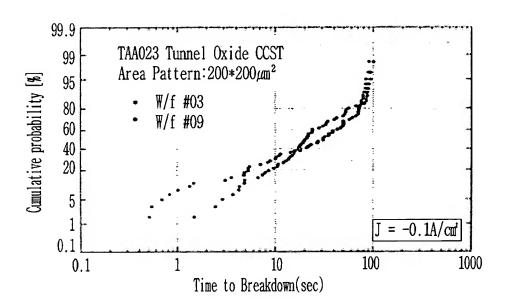
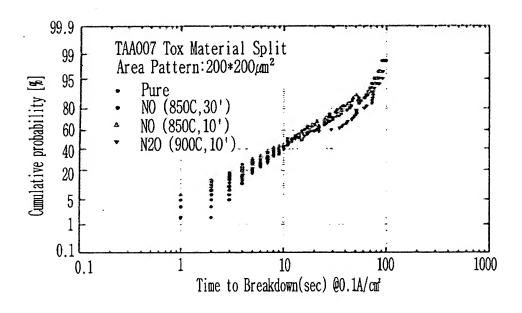


FIG. 3 (PRIOR ART)



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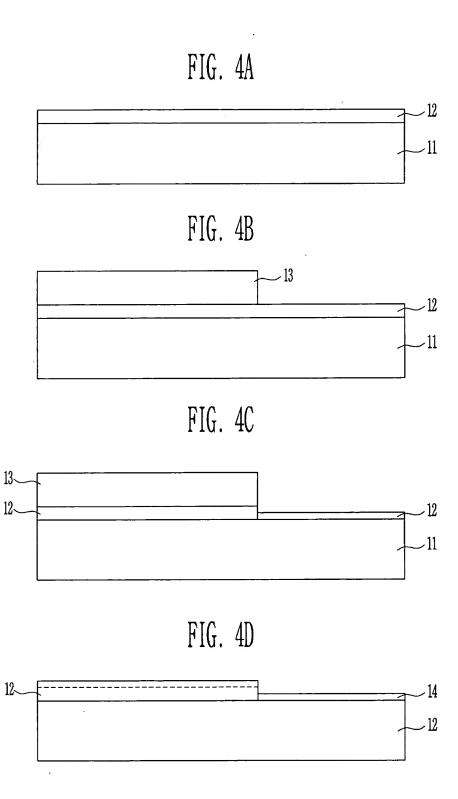


FIG. 5

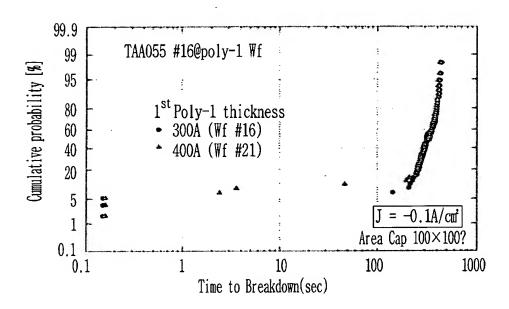


FIG. 6

		208	278	427	263	285		
	352	430	424	228	462	273	394	
317	369	336	234	215	309	404	390	321
000	440	311	301	387	306	269	368	425
	401	306	354	282	313	492	419	403
000	315	398	390	251	463	397	289	267
	311	448	314	457	294	294	253	
		144	386	377	447	396		